

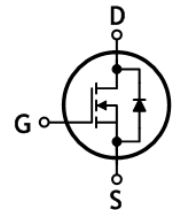
## SWITCHING REGULATOR APPLICATION

### Features

- Drain-Source breakdown voltage:  $V_{DSS}=650V$  (Min.)
- Low gate charge:  $Q_g=14nC$  (Typ.)
- Low drain-source On resistance:  $R_{DS(on)}=1.8\Omega$
- 100% avalanche tested
- RoHS compliant device

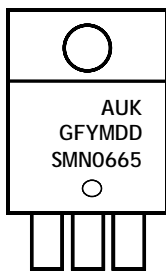
### Ordering Information

Part Number	Marking	Package
SMN0665FD	SMN0665	TO-220F-3L



TO-220F-3L

### Marking Information



Column 1: Manufacturer  
 Column 2: Production Information  
 e.g.) GFYMDD  
 -. G: Option Code (H: Halogen Free)  
 -. F: Factory Management Code  
 -. YMDD: Date Code (Year, Month, Date)  
 Column 3: Device Code

### Absolute maximum ratings ( $T_C=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	650	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current (DC) *	$I_D$	$T_C=25^\circ C$	5.5	A
		$T_C=100^\circ C$	3.48	A
Drain current (Pulsed) *	$I_{DM}$	22	A	
Single avalanche current <sup>(Note 2)</sup>	$I_{AS}$	5.5	A	
Single pulsed avalanche energy <sup>(Note 2)</sup>	$E_{AS}$	245	mJ	
Repetitive avalanche current <sup>(Note 1)</sup>	$I_{AR}$	5.5	A	
Repetitive avalanche energy <sup>(Note 1)</sup>	$E_{AR}$	4.8	mJ	
Power dissipation	$P_D$	48	W	
Junction temperature	$T_J$	150	$^\circ C$	
Storage temperature range	$T_{stg}$	-55-150	$^\circ C$	

\* Limited only maximum junction temperature

## Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 2.6	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	$BV_{DSS}$	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ , $V_{DS}=V_{GS}$	3	4	5	V
Drain-source cut-off current	$I_{DSS}$	$V_{DS}=650\text{V}$ , $V_{GS}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate leakage current	$I_{GSS}$	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 30\text{V}$	-	-	$\pm 100$	nA
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ , $I_D=2.75\text{A}$	-	1.8	2.2	$\Omega$
Forward transfer conductance (Note 3)	$g_{fs}$	$V_{DS}=10\text{V}$ , $I_D=2.75\text{A}$	-	4	-	S
Input capacitance	$C_{iss}$	$V_{DS}=25\text{V}$ , $V_{GS}=0\text{V}$ , $f=1.0\text{MHz}$	-	760	1046	pF
Output capacitance	$C_{oss}$		-	67	92	
Reverse transfer capacitance	$C_{rss}$		-	9	12	
Turn-on delay time (Note 3,4)	$t_{d(on)}$	$V_{DD}=325\text{V}$ , $I_D=5.5\text{A}$ , $R_G=25\Omega$	-	55	128	ns
Rise time (Note 3,4)	$t_r$		-	79	174	
Turn-off delay time (Note 3,4)	$t_{d(off)}$		-	94	208	
Fall time (Note 3,4)	$t_f$		-	33	75	
Total gate charge (Note 3,4)	$Q_g$	$V_{DS}=520\text{V}$ , $V_{GS}=10\text{V}$ , $I_D=5.5\text{A}$	-	14	20	nC
Gate-source charge (Note 3,4)	$Q_{gs}$		-	6	-	
Gate-drain charge (Note 3,4)	$Q_{gd}$		-	4	-	

Source-Drain Diode Ratings and Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	$I_S$	Integral reverse diode in the MOSFET	-	-	5.5	A
Source current (Pulsed)	$I_{SM}$		-	-	22	A
Forward voltage	$V_{SD}$	$V_{GS}=0\text{V}$ , $I_S=5.5\text{A}$	-	-	1.4	V
Reverse recovery time (Note 3,4)	$t_{rr}$	$I_S=5.5\text{A}$ , $V_{GS}=0\text{V}$ $di_F/dt=100\text{A}/\mu\text{s}$	-	494	-	ns
Reverse recovery charge (Note 3,4)	$Q_{rr}$		-	2	-	$\mu\text{C}$

Note:

1. Repeated rating: Pulse width limited by safe operating area
2.  $L=15\text{mH}$ ,  $I_{AS}=5.5\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
3. Pulse test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
4. Essentially independent of operating temperature typical characteristics

## Electrical Characteristics Curves

Fig. 1  $I_D - V_{DS}$

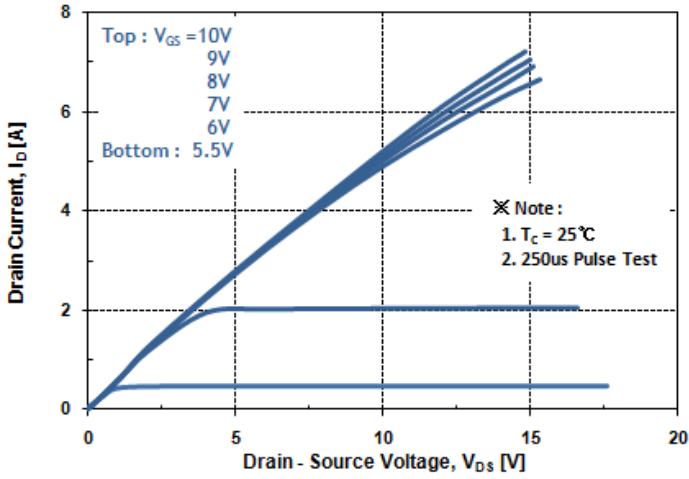


Fig. 2  $I_D - V_{GS}$

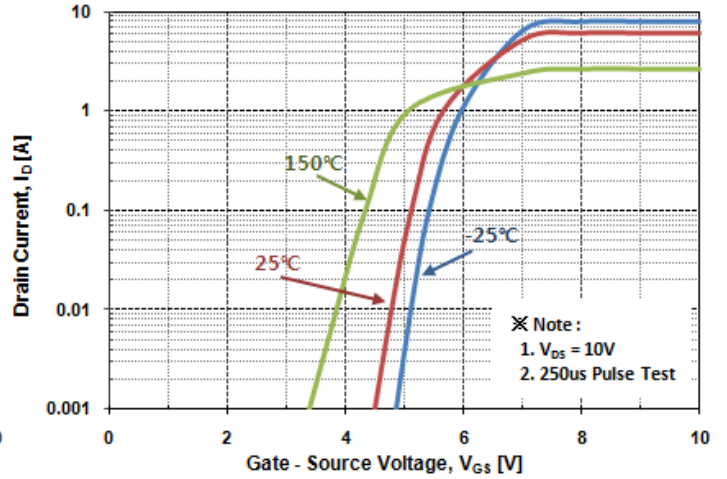


Fig. 3  $R_{DS(ON)} - I_D$

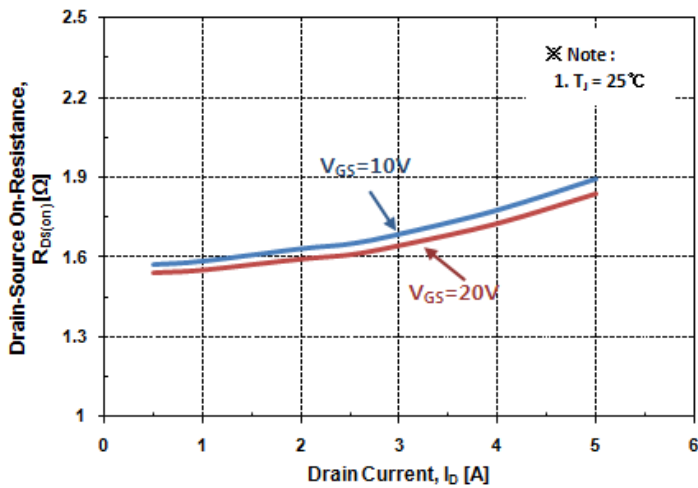


Fig. 4  $I_S - V_{SD}$

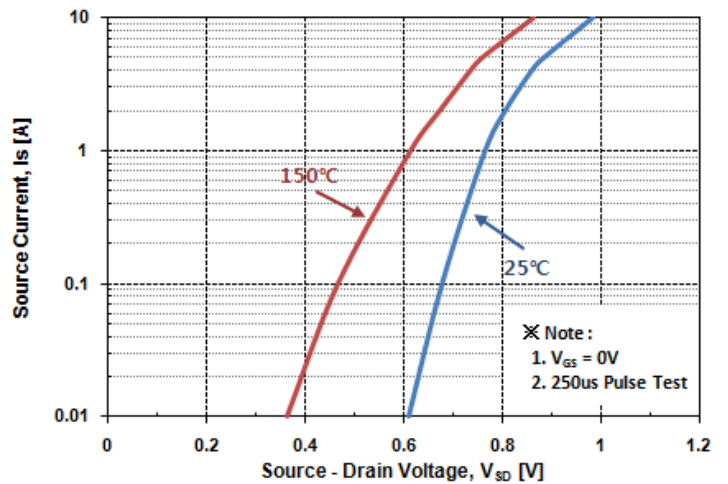


Fig. 5 Capacitance -  $V_{DS}$

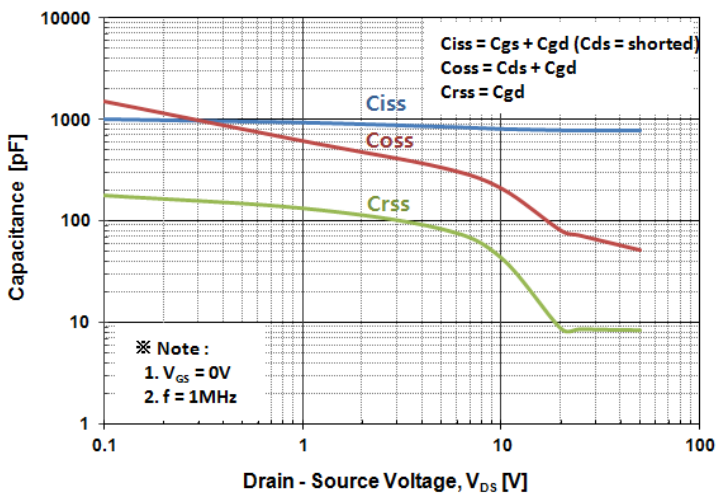


Fig. 6  $V_{GS} - Q_G$

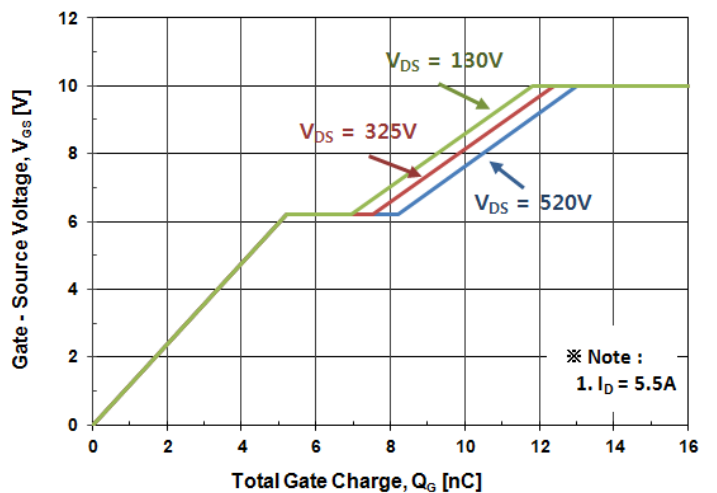


Fig. 7  $BV_{DSS} - T_J$

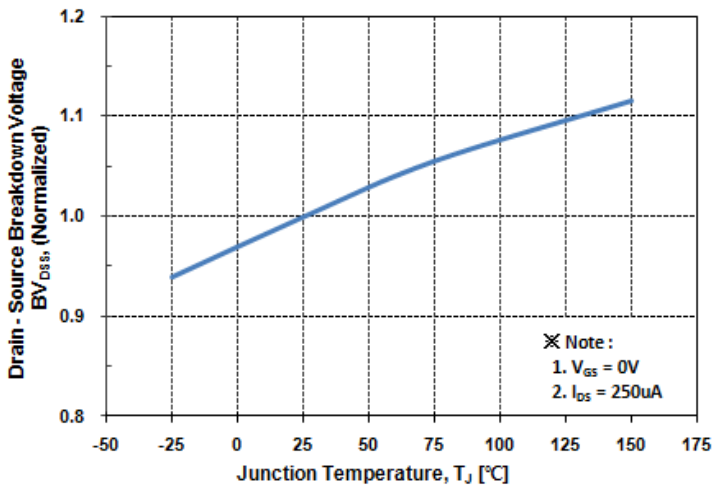


Fig. 8  $R_{DS(on)} - T_J$

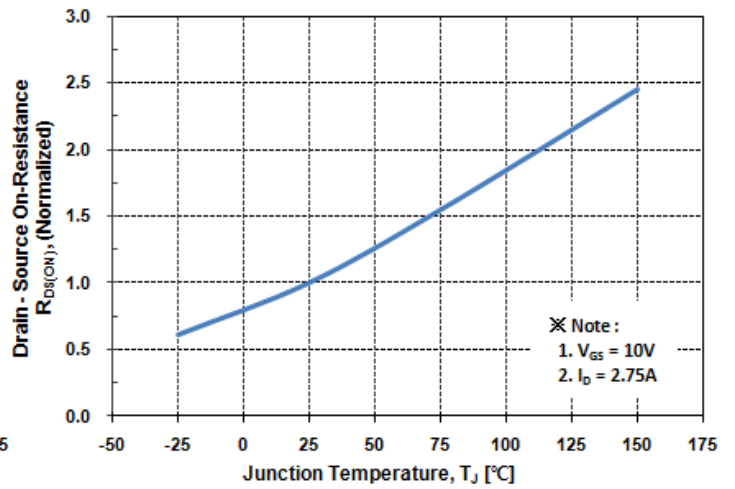


Fig. 9  $I_D - T_C$

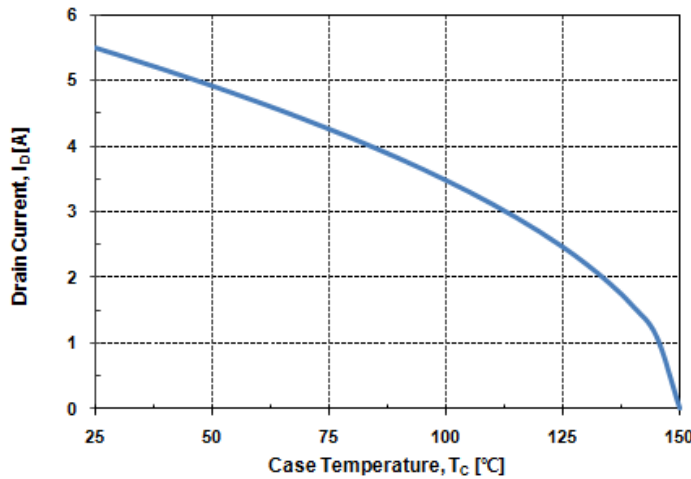


Fig. 10 Safe Operating Area

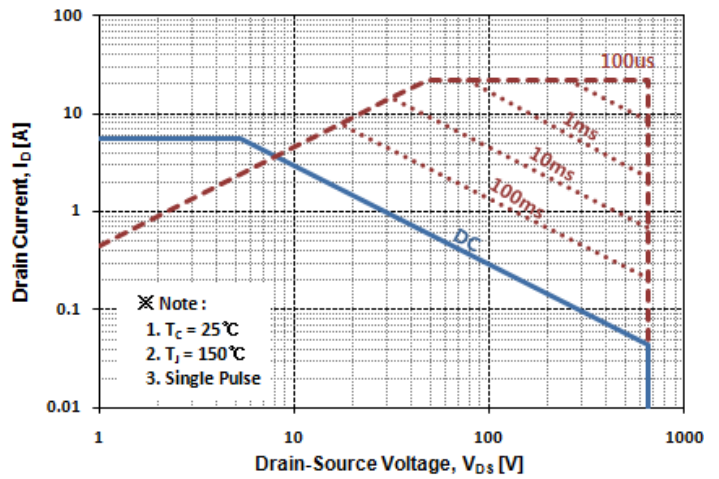


Fig. 11 Transient Thermal Impedance

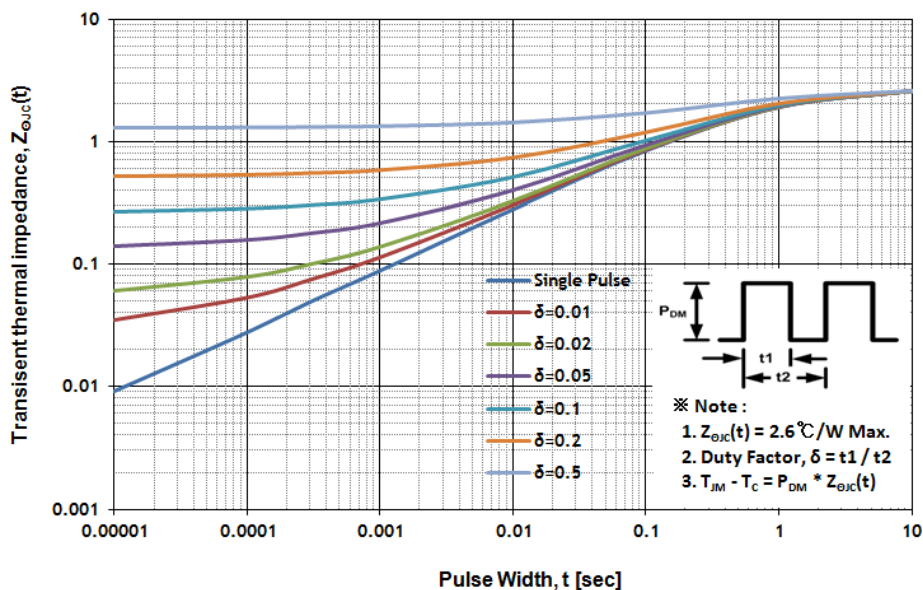


Fig. 12 Gate Charge Test Circuit & Waveform

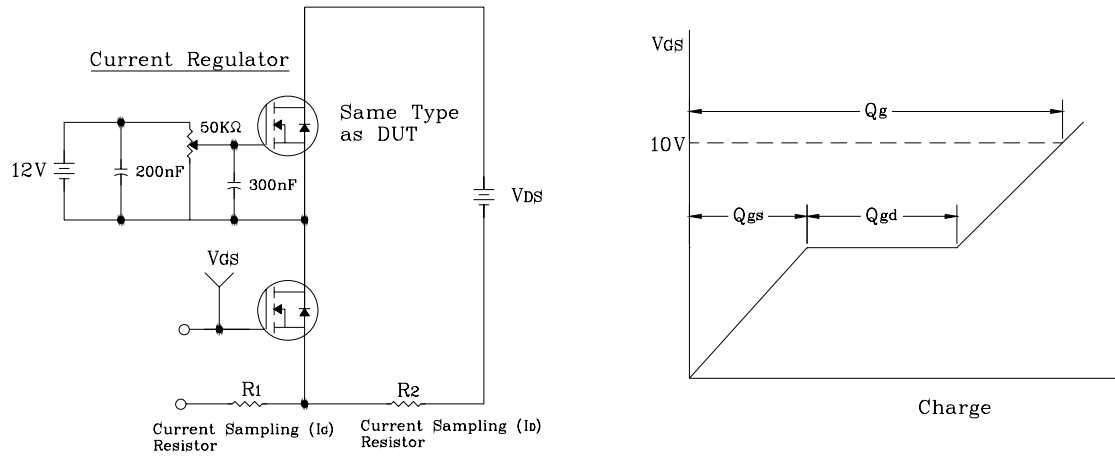


Fig. 13 Resistive Switching Test Circuit & Waveform

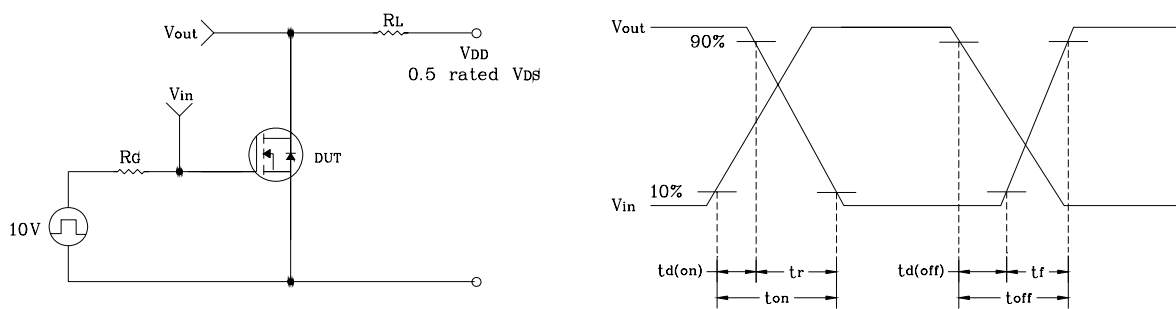


Fig. 14 E<sub>AS</sub> Test Circuit & Waveform

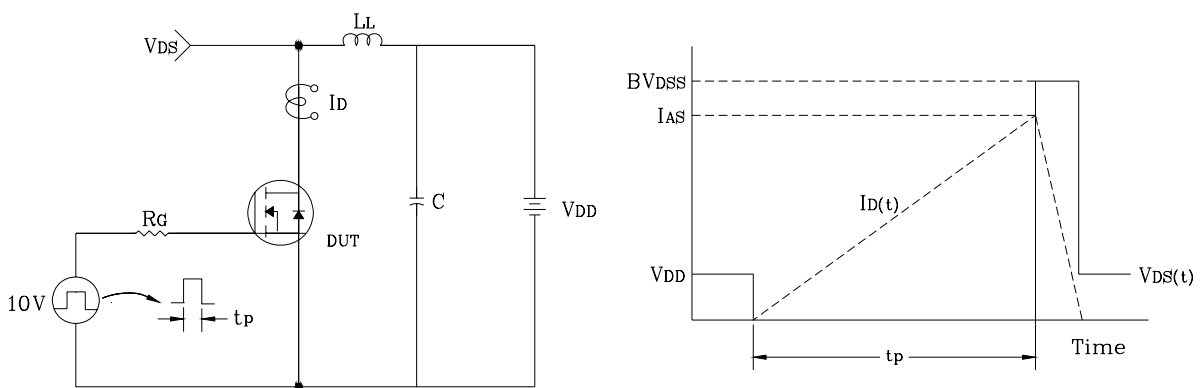
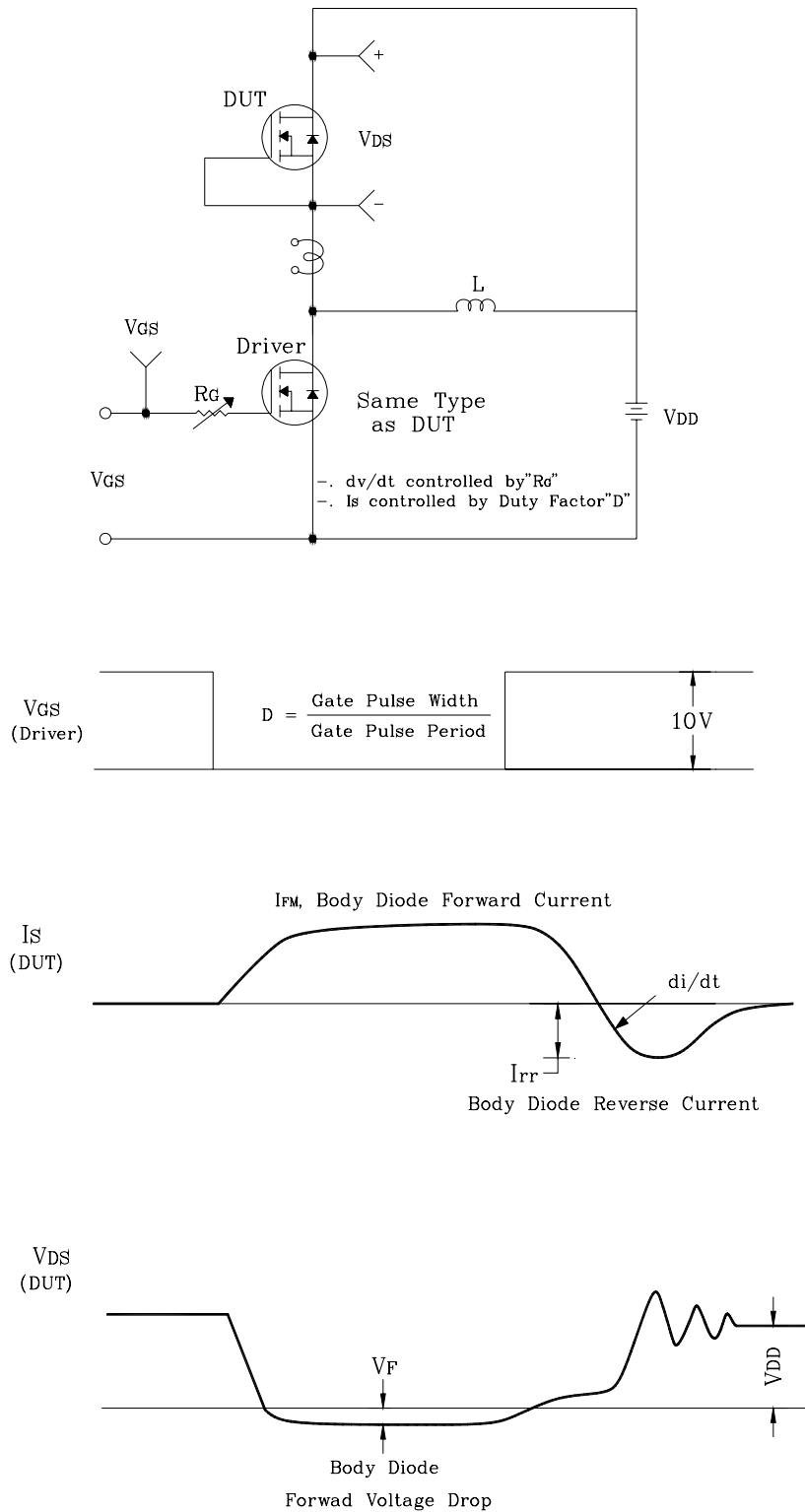
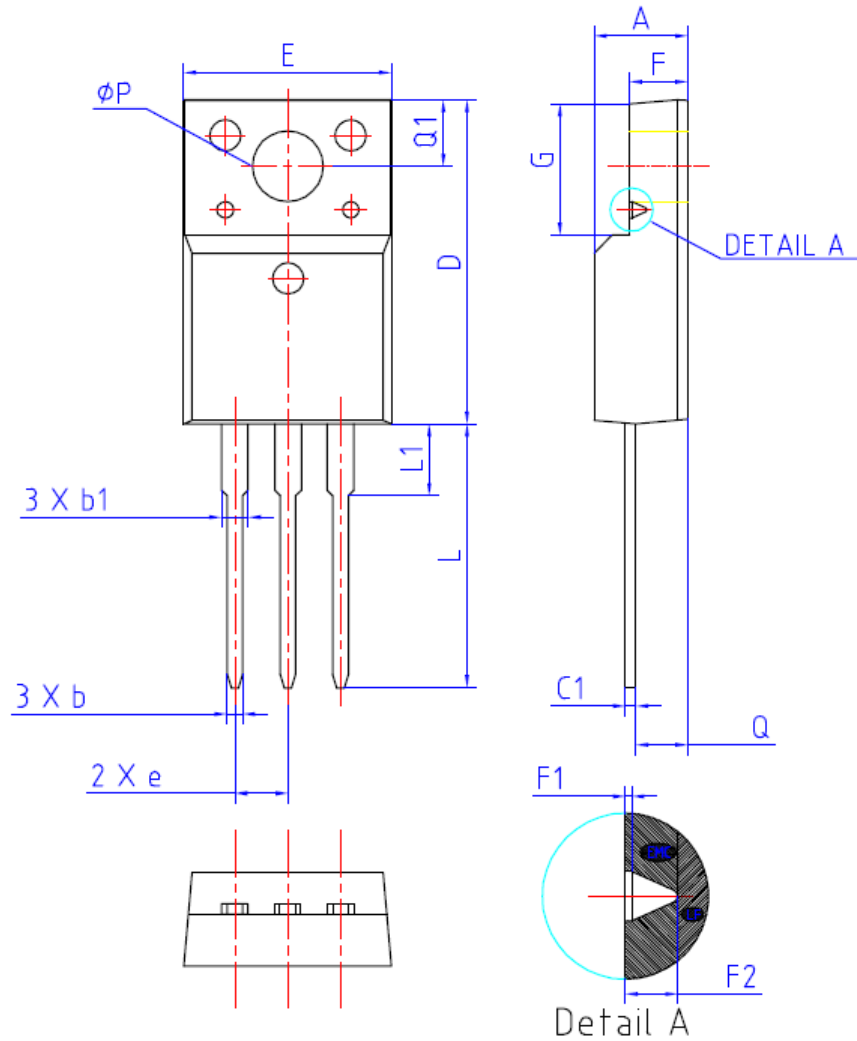


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	4.50	4.70	4.90	
b	0.70	0.80	0.90	
b1	1.33	1.40	1.47	
C1	0.45	0.50	0.60	
D	15.67	15.87	16.07	
E	9.96	10.16	10.36	
e	2.54BSC			
F	2.34	2.54	2.74	
F1	(0.10 REF)			
F2	(0.84 REF)			
G	6.48	6.68	6.88	
L	12.78	12.98	13.18	
L1	3.03	3.23	3.43	
Q	2.56	2.76	2.96	
Q1	3.10	3.30	3.50	
$\phi P$	3.08	3.18	3.28	

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